

GENERAL PURPOSE APPLICATION. SWITCHING APPLICATION.

FEATURES

- A super-minimold package houses 2 transistor.
- Excellent temperature response between these 2 transistor.
- High pairing property in h_{FE} .
- The following characteristics are common for Q_1 , Q_2 .
- Suffix U : Qualified to AEC-Q101.
ex) KTC812E-Y-RTK/HU

MAXIMUM RATING (Ta=25 °C)

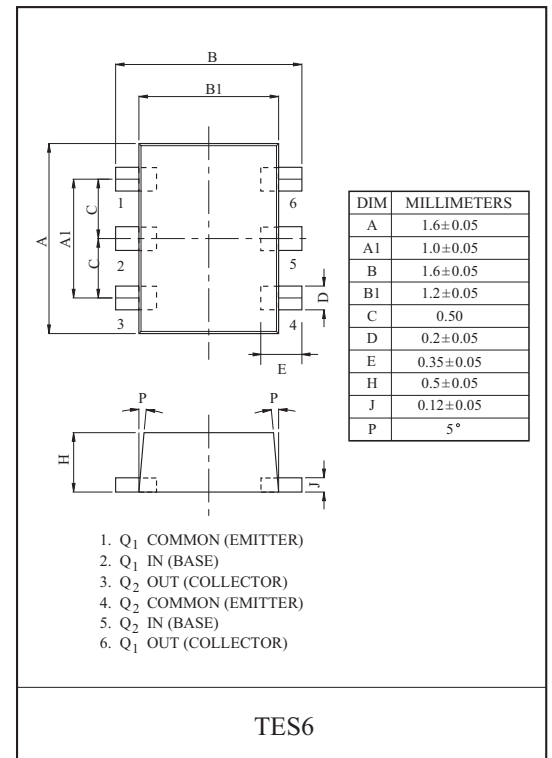
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Base Current	I_B	30	mA
Collector Power Dissipation	P_C^*	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

* Total Rating

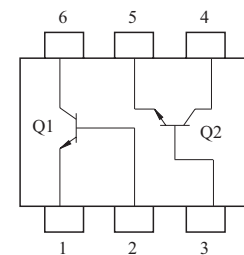
ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT.
Collector Cut-off Current	I_{CBO}	$V_{CB}=60V$, $I_E=0$	-	-	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V$, $I_C=0$	-	-	0.1	μA
DC Current Gain	h_{FE} (Note)	$V_{CE}=6V$, $I_C=2mA$	120	-	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA$, $I_B=10mA$	-	0.1	0.3	V
Transition Frequency	f_T	$V_{CE}=10V$, $I_C=1mA$	80	-	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$, $I_E=0$, $f=1MHz$	-	2	3.5	pF
Noise Figure	NF	$V_{CE}=6V$, $I_C=0.1mA$, $f=1kHz$, $R_g=10k\Omega$	-	1.0	10	dB

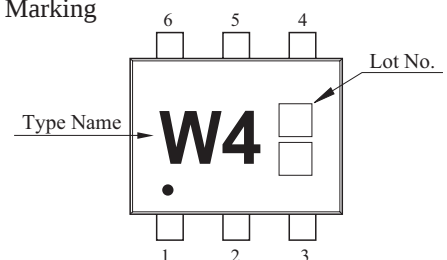
Note : h_{FE} Classification Y(4):120 240, GR(6):200 400



EQUIVALENT CIRCUIT (TOP VIEW)



Marking



KTC812E

